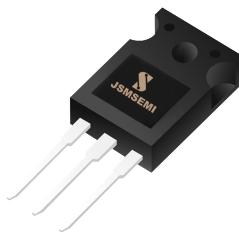


FEATURES

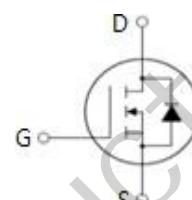
- ★ Fast switching
- ★ 100% avalanche tested
- ★ Improved dv/dt capability



APPLICATIONS

- ★ Switch Mode Power Supply (SMPS)
- ★ Uninterruptible Power Supply (UPS)
- ★ Hard switched and high frequency circuits

Device Marking and Package Information		
Device	Package	Marking
IRFP7430PBF	TO-247	IRFP7430



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-247	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	40	V
Continuous Drain Current $V_{GS} = 10\text{V}$ $T_C = 25^\circ\text{C}$	I_D	192 (note5)	A
Pulsed Drain Current (note1)	I_{DM}	648	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	1980	mJ
Avalanche Current (note1)	I_{AS}	95	A
Repetitive Avalanche Energy (note1)	E_{AR}	1188	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	241	W
Peak Diode Recovery dv/dt (note1)	dv/dt	5.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.73	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 40\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	20	μA
		$V_{\text{DS}} = 32\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$	--	--	250	
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}$	--	--	± 200	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 60\text{A}$ (Note4)	--	3	4	$\text{m}\Omega$
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	3840	--	pF
Output Capacitance	C_{oss}		--	1710	--	
Reverse Transfer Capacitance	C_{rss}		--	470	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 20\text{V}, I_D = 192\text{A}, V_{\text{GS}} = 10\text{V}$ (Note4)	--	96	--	nC
Gate-Source Charge	Q_{gs}		--	19	--	
Gate-Drain Charge	Q_{gd}		--	46	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 20\text{V}, I_D = 192\text{A}, R_G = 10 \Omega, V_{\text{GS}} = 10\text{V}$ (Note4)	--	32	--	ns
Turn-on Rise Time	t_r		--	92	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	101	--	
Turn-off Fall Time	t_f		--	69	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	192	A
Pulsed Diode Forward Current	I_{SM}		--	--	650	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 60\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.3	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_S = 192\text{A}, dI/dt = 100\text{A}/\mu\text{s}$	--	78	--	ns
Reverse Recovery Charge	Q_{rr}		--	200	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Starting $T_J = 25^\circ\text{C}, L=1\text{mH}, V_{\text{DD}} = 20\text{V}$
3. $I_{\text{SD}} \leq 95\text{A}, di/dt \leq 150\text{A/us}, V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}, T_J = 175^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Calculated continuous current based on maximum allowable junction temperature, Package limitation current is 75A

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

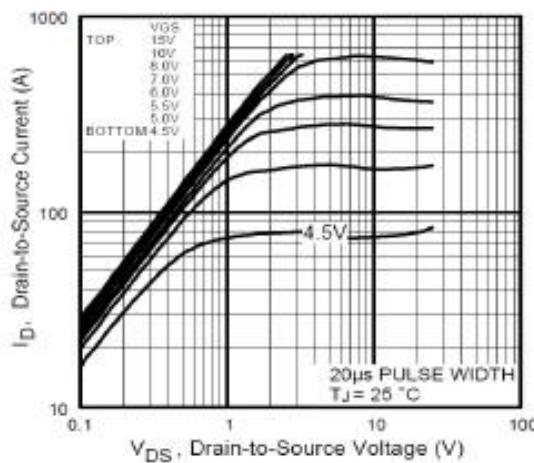


Fig 1. Typical Output Characteristics

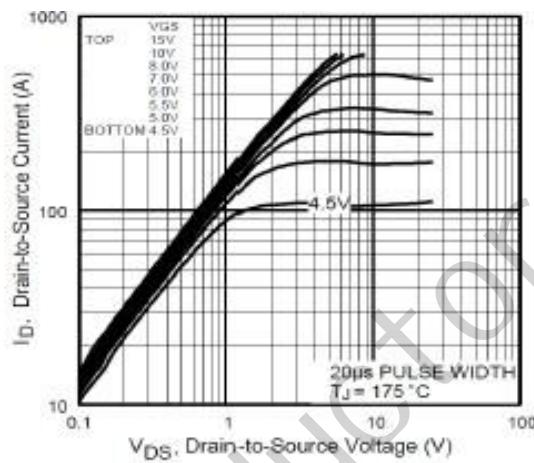


Fig 2. Typical Output Characteristics

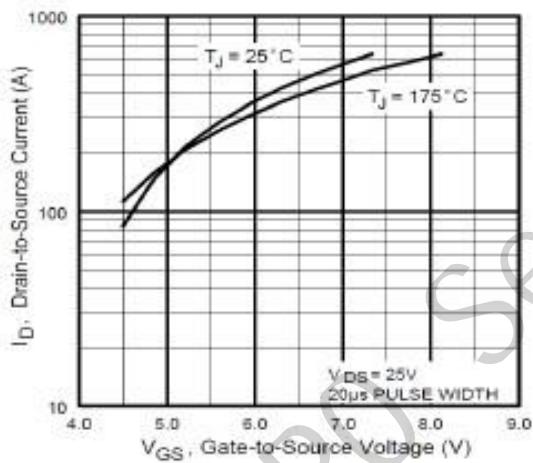


Fig 3. Typical Transfer Characteristics

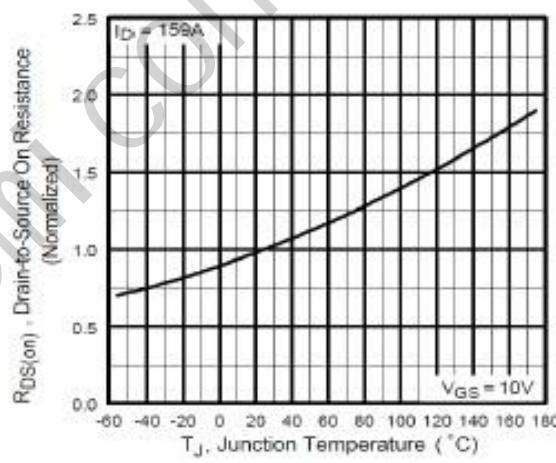


Fig 4. Normalized On-Resistance
Vs. Temperature

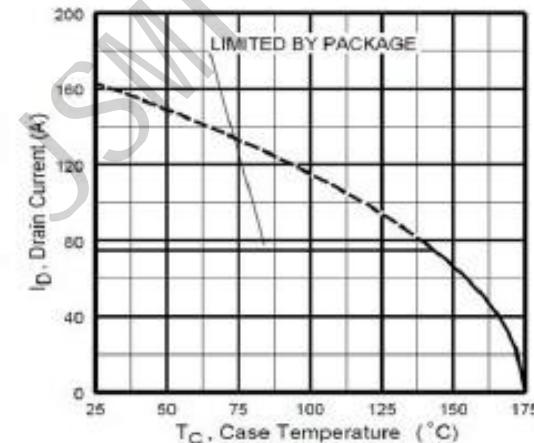


Fig 5. Maximum Drain Current Vs.
Case Temperature

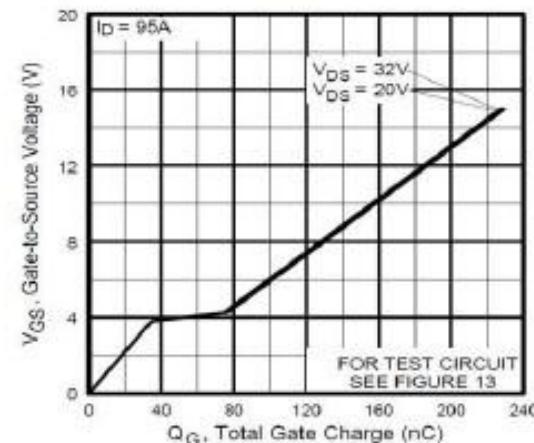


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

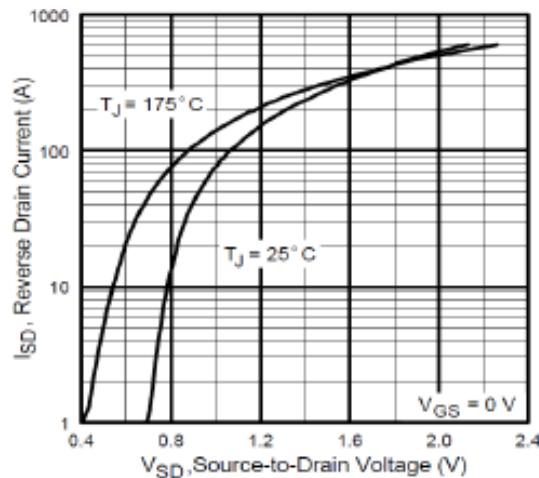


Fig 7. Typical Source-Drain Diode Forward Voltage

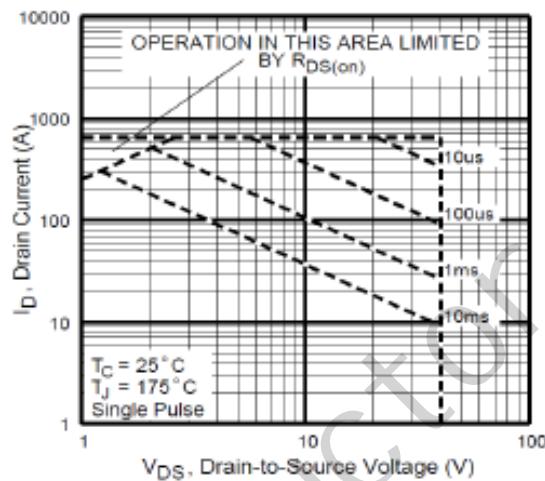


Fig 8. Maximum Safe Operating Area

Figure A: Gate Charge Test Circuit and Waveform

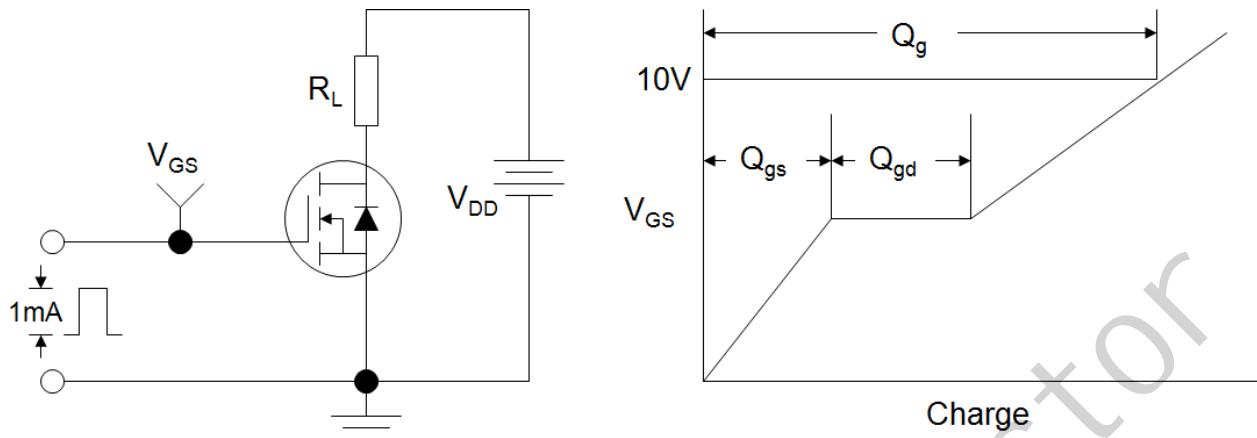


Figure B: Resistive Switching Test Circuit and Waveform

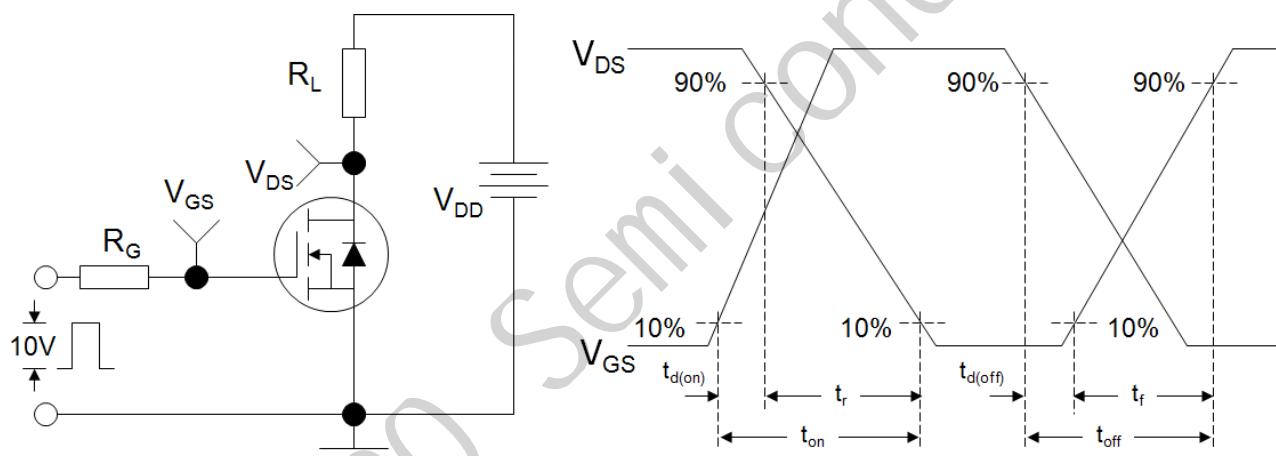
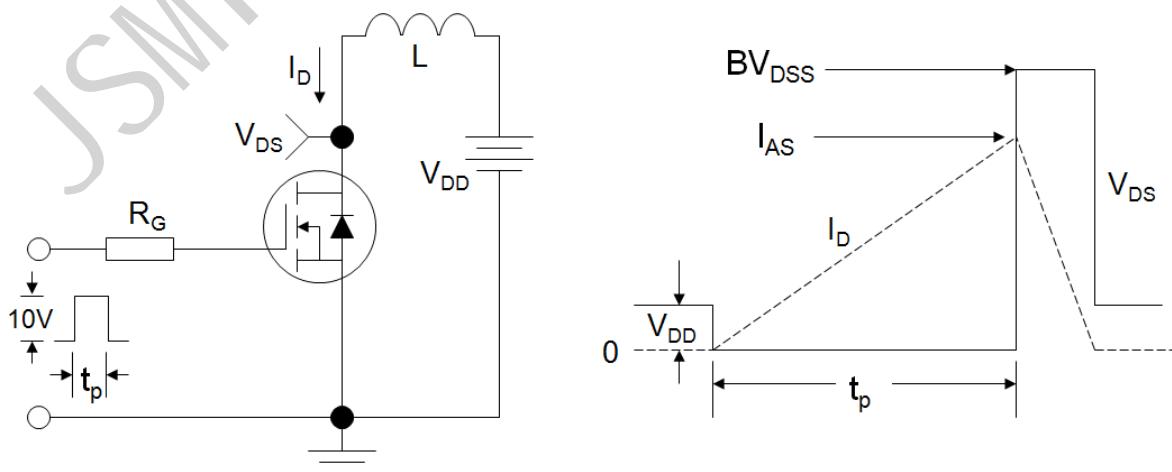
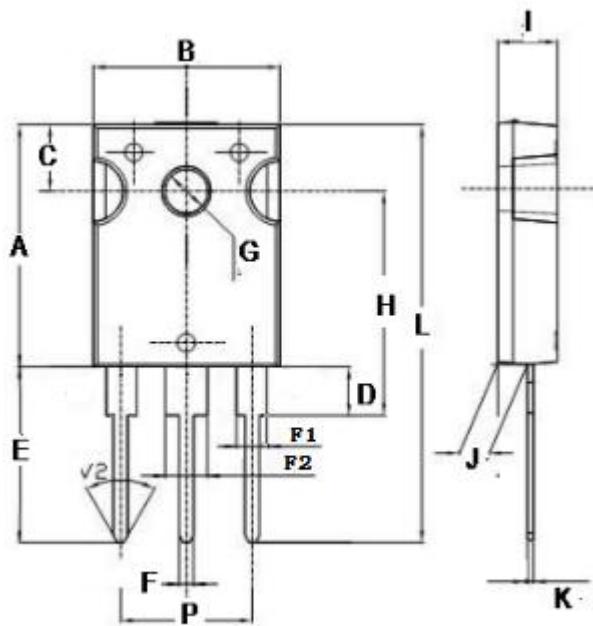


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-247 Package Dimensions



Dim	Min	Max
A	20.0	22.0
B	15.5	16.0
C	5.7	6.3
D	4.0	4.4
E	19.0	21.0
F	1.1	1.3
G	3.5	3.8
H	18.3	20.2
I	4.9	5.2
J	2.3	2.5
K	0.55	0.65
L	39.0	42.0
P	10.7	10.9
F1	1.9	2.1
F2	2.9	3.1
mm		

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)